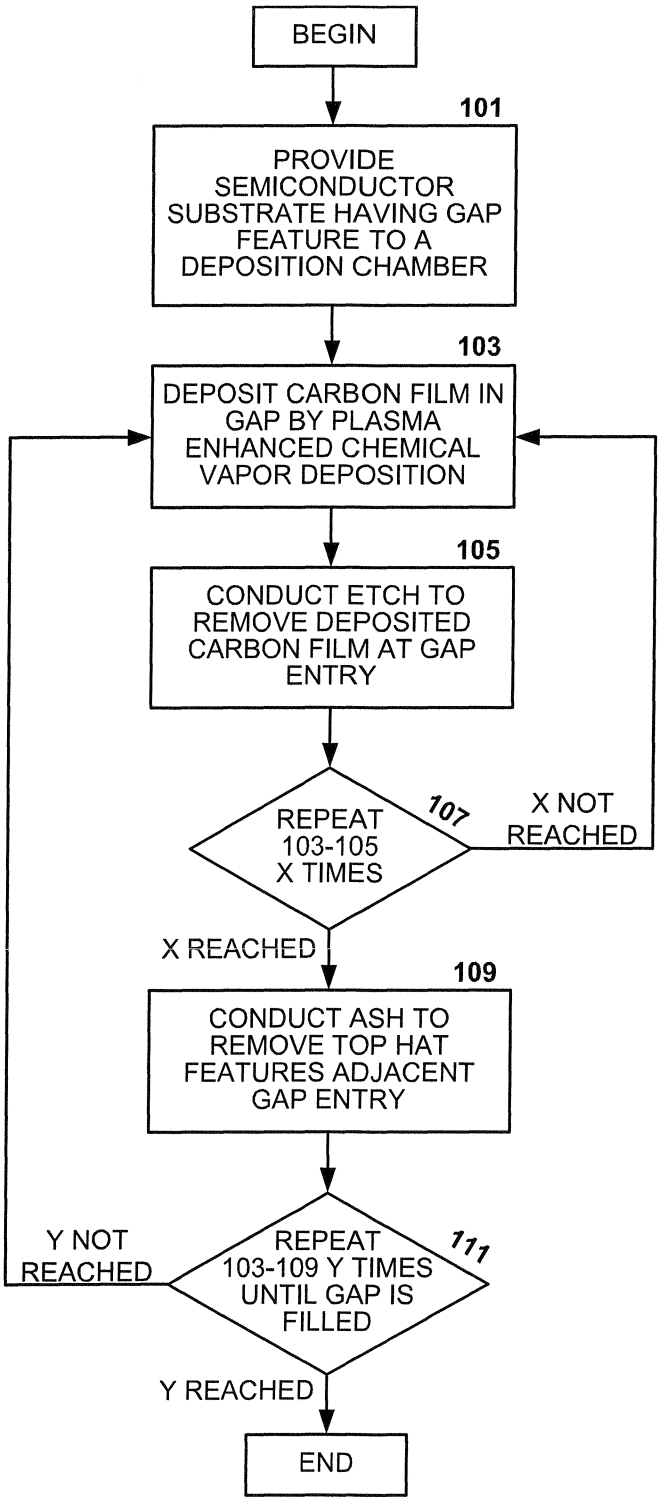

BEGIN
101
PROVIDE SEMICONDUCTOR SUBSTRATE HAVING GAP FEATURE TO A DEPOSITION CHAMBER
103
DEPOSIT CARBON FILM IN GAP BY PLASMA ENHANCED CHEMICAL VAPOR DEPOSITION
105
CONDUCT ETCH TO REMOVE DEPOSITED CARBON FILM AT GAP ENTRY
REPEAT 103-105 X TIMES
107
X NOT REACHED
X REACHED
109
CONDUCT ASH TO REMOVE TOP HAT FEATURES ADJACENT GAP ENTRY
REPEAT 103-109 Y TIMES UNTIL GAP IS FILLED
111
Y NOT REACHED
Y REACHED
END

FIG. 1

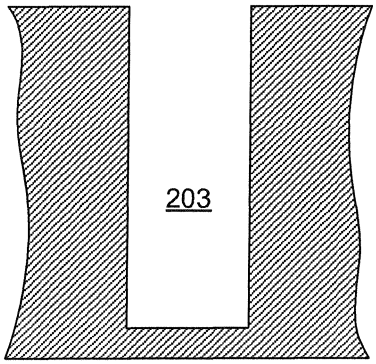


FIG. 2A

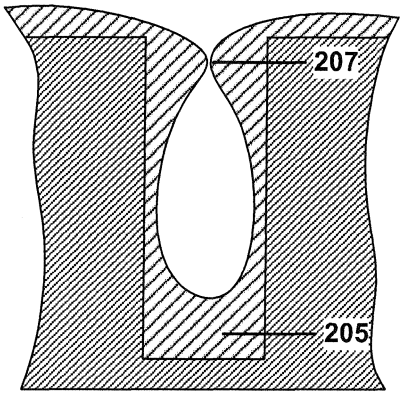


FIG. 2B

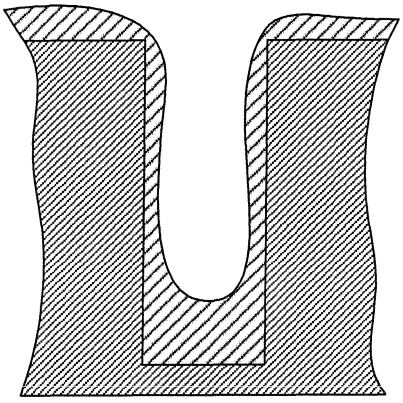


FIG. 2C

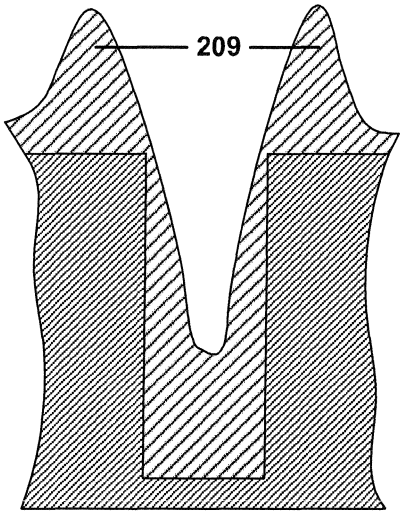


FIG. 2D

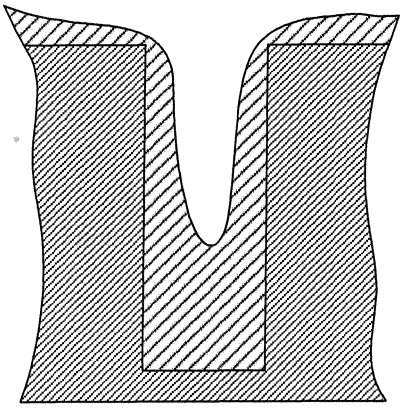


FIG. 2E

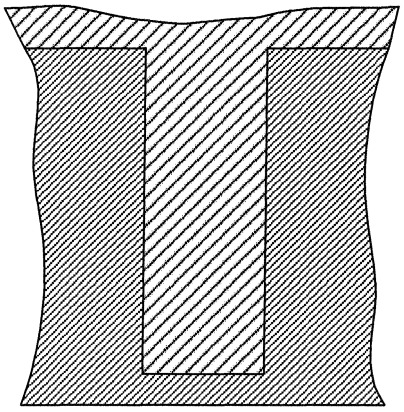


FIG. 2F

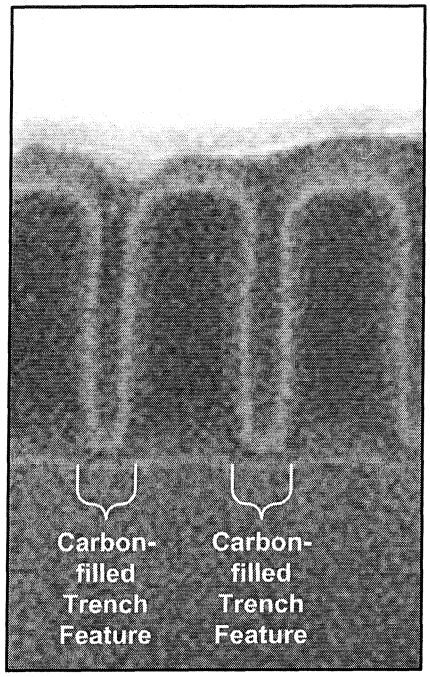


FIG. 3A

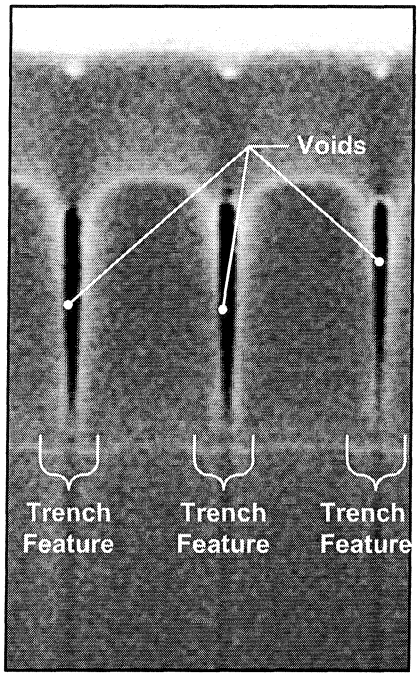


FIG. 3B

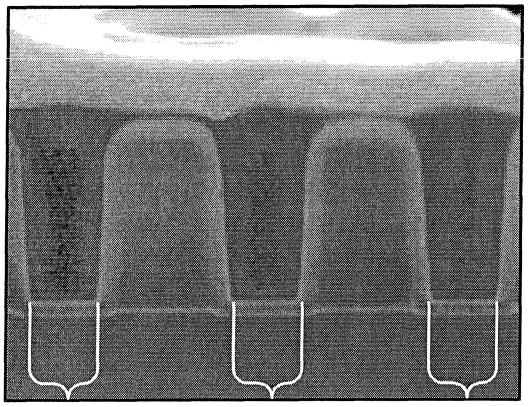


FIG. 4A

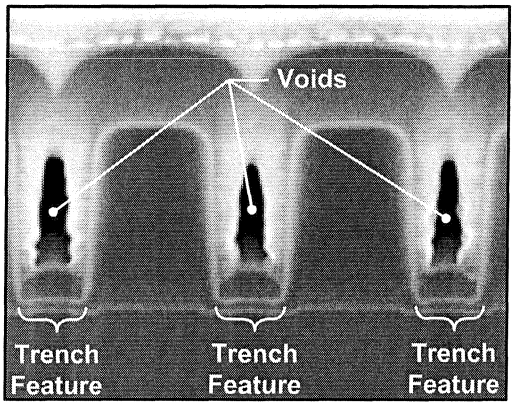


FIG. 4B

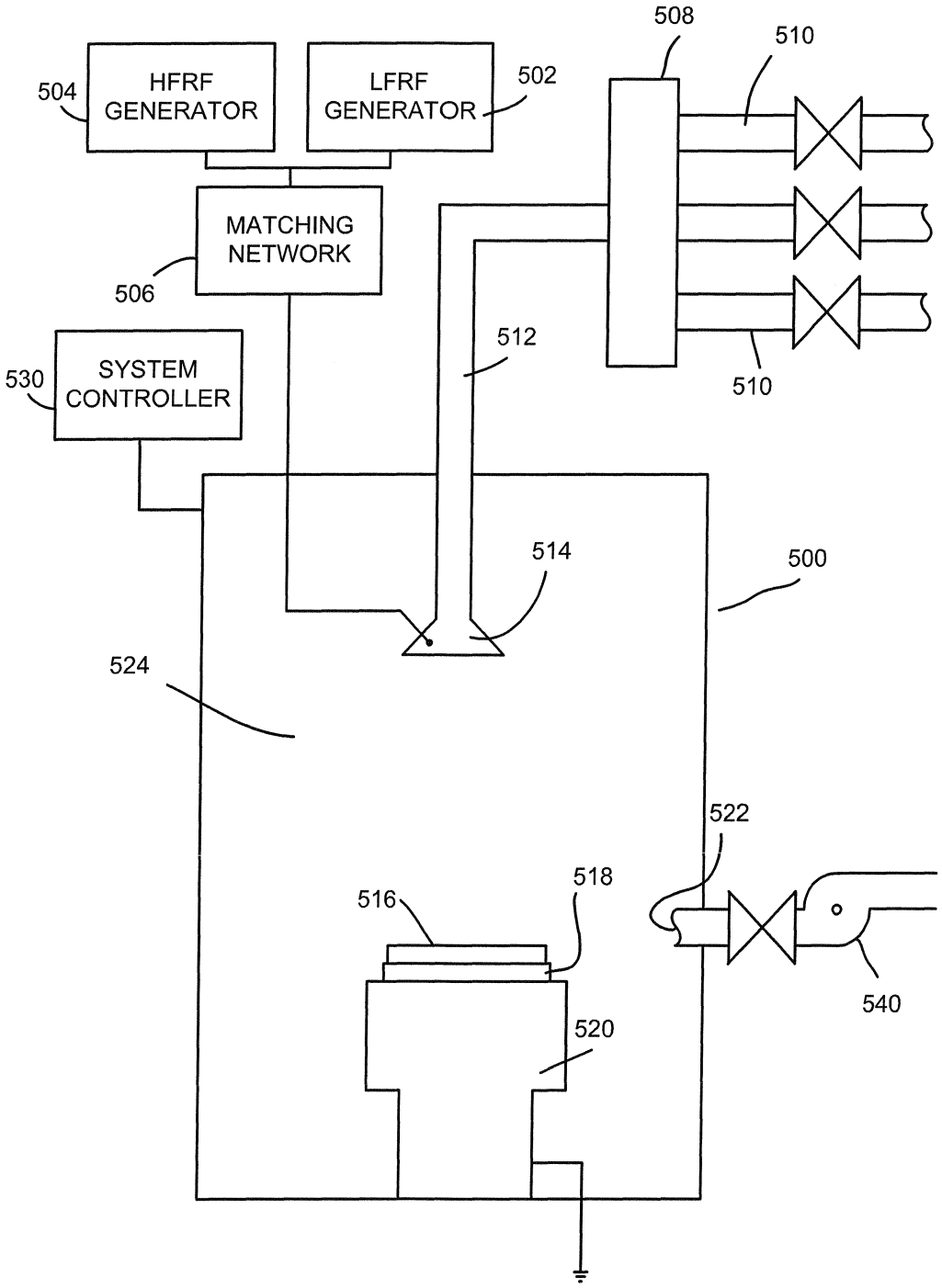

HFRF GENERATOR
LFRF GENERATOR
MATCHING NETWORK
SYSTEM CONTROLLER
504
502
506
530
508
510
512
514
500
524
522
518
516
520
540

FIG. 5